

## ESDLC24VD3B

## Description

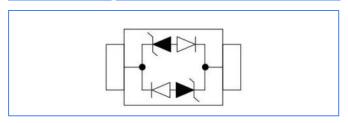
ESDLC24VD3B is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, ultra-low capacitance values, it is very suitable for signal port and board space speed transmission is very small places, such as Ethernet, mobile phones, MP3 players, digital cameras and other portable.

#### Features

- Ultra low leakage: nA levelOperating voltage: 24VPackage: SOD-323
- Protects one I/O line (unidirection)
- Low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±15kV
    - Contact discharge: ±8kV
  - IEC61000-4-4 (EFT) 40A (5/50ns)
  - IEC61000-4-5 (Lightning) 12A (8/20µs)



## Functional Diagram



#### **Applications**

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Peripherals
- USB Interface

#### Absolute Maximum Ratings(Tamb=25°C unless otherwise specified)

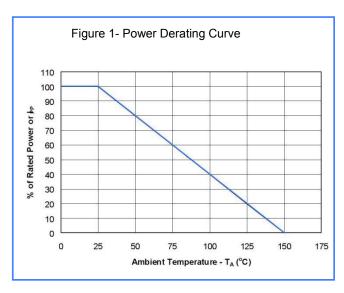
Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	P <sub>PP</sub>	350	Watts	
ESD per IEC 61000-4-2 (Air)		±15	KV	
ESD per IEC 61000-4-2 (Contact)	- V <sub>ESD</sub>	±8	KV	
Lead Soldering Temperature	T∟	260 (10 sec)	°C	
Operating Temperature Range	T₃	-55 to +150	°C	
Storage Temperature Range	T <sub>STJ</sub>	-55 to +150	°C	

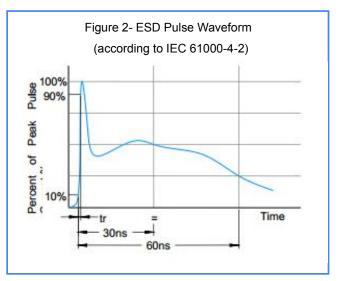


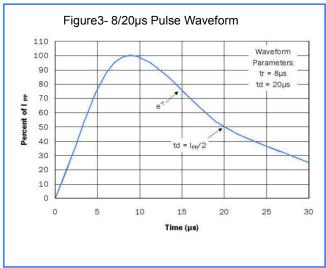
# Electrical Characteristics (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	$V_{\scriptscriptstyle RWM}$				24	V
Reverse Breakdown Voltage	$V_{\scriptscriptstyle BR}$	I <sub>t</sub> = 1mA		26.7		V
Reverse Leakage Current	<b>I</b> <sub>R</sub>	V <sub>R</sub> =V <sub>RWM</sub>			1	μΑ
Clamping Voltage	Vc	$I_{PP}=1A$ , $t_{P}=8/20\mu s$			43	V
		I <sub>PP</sub> =3A, t <sub>P</sub> = 8/20μs			56	V
Junction Capacitance	<b>C</b> <sub>J</sub>	V <sub>R</sub> =0V, f = 1MHz		1		pF

# Characteristics Curves

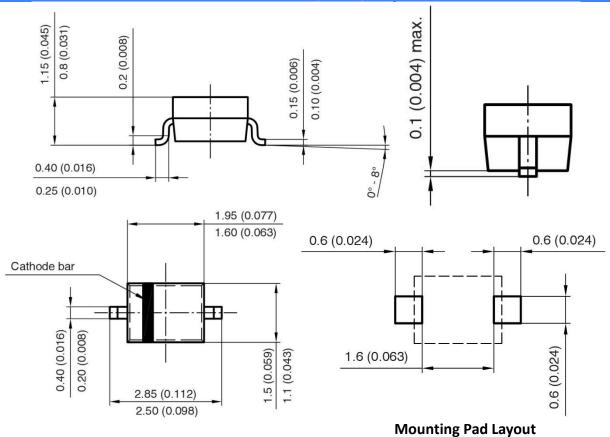












# Disclaimer

Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.

Users should verify actual device performance in their specific applications.

单击下面可查看定价,库存,交付和生命周期等信息

>>Yint(音特电子)